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(54) Title: THIN FILM TRANSISTOR SUBSTRATE AND METHOD FOR FORMING METAL WIRE THEREOF



(57) Abstract: The present invention relates to a thin film transistor substrate and a metal wiring method thereof, more particularly to a thin film transistor substrate comprising self-assembled monolayers between the substrate and the metal wiring, and a metal wiring method thereof. Since a thin film transistor substrate of the present invention comprises three-dimensionally cross-linked self-assembled monolayers between the Si surface and the metal wiring, it has good adhesion ability and anti-diffusion ability.